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(54) **SOLID STATE DEVICE MINIATURIZATION**

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Related U.S. Application Data

(57) **ABSTRACT**

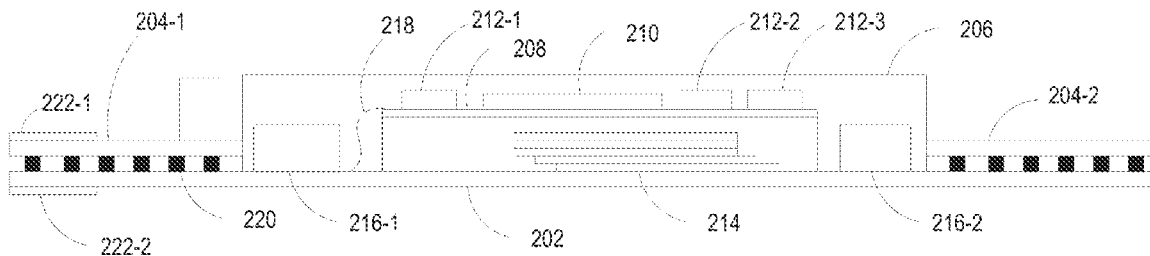
(63) Continuation of application No. 14/978,315, filed on Dec. 22, 2015, now Pat. No. 9,773,764.

One or more example embodiments of miniaturized electric devices are disclosed. In some example embodiments, the electric device includes a first thin substrate layer and a second thin substrate layer positioned above the first thin substrate layer. The electric device further includes one or more components electrically coupled to the first thin substrate layer. An overmold compound is deposited covering the one or more components between the first thin substrate and the second thin substrate. The electric device further includes one or more through mold vias that electrically and communicatively connect the first thin substrate layer and the second thin substrate layer.

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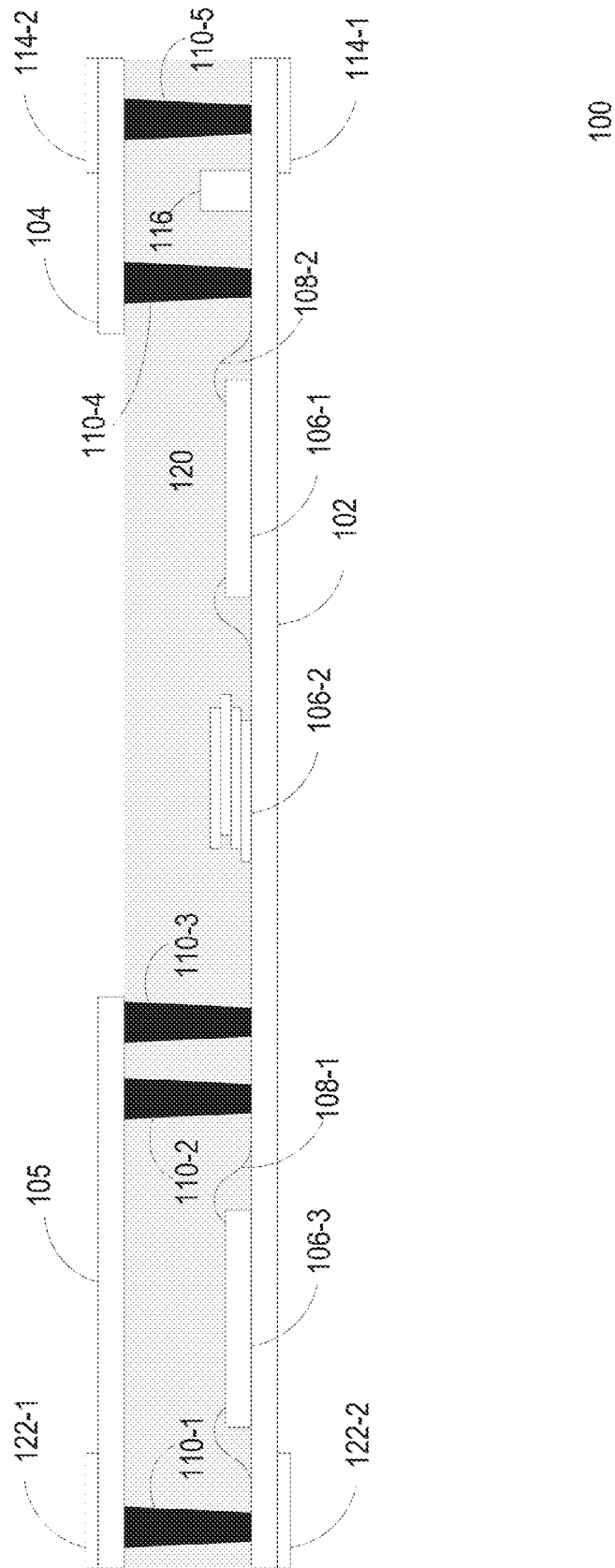
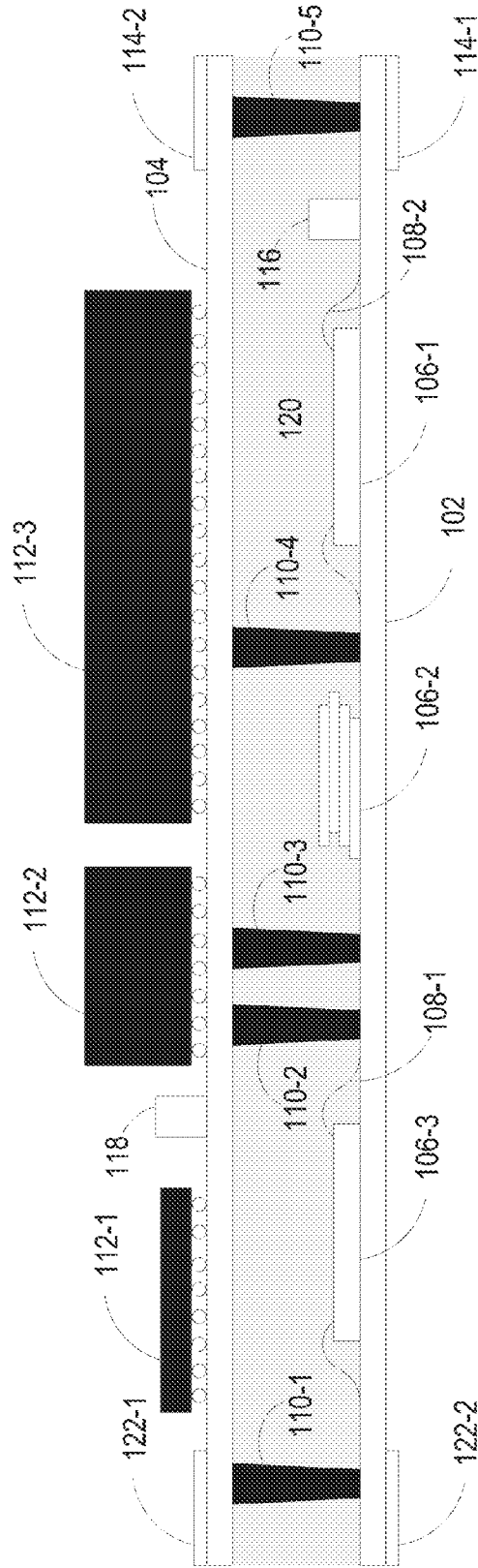


FIG. 1A



100

FIG. 1B

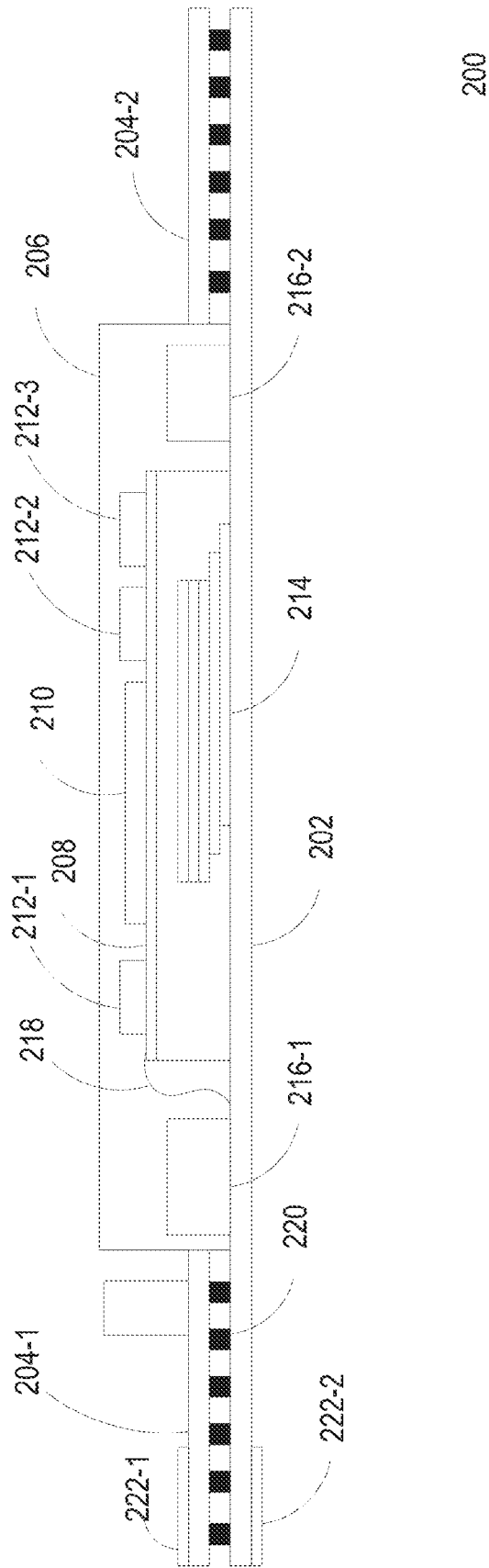


FIG. 2

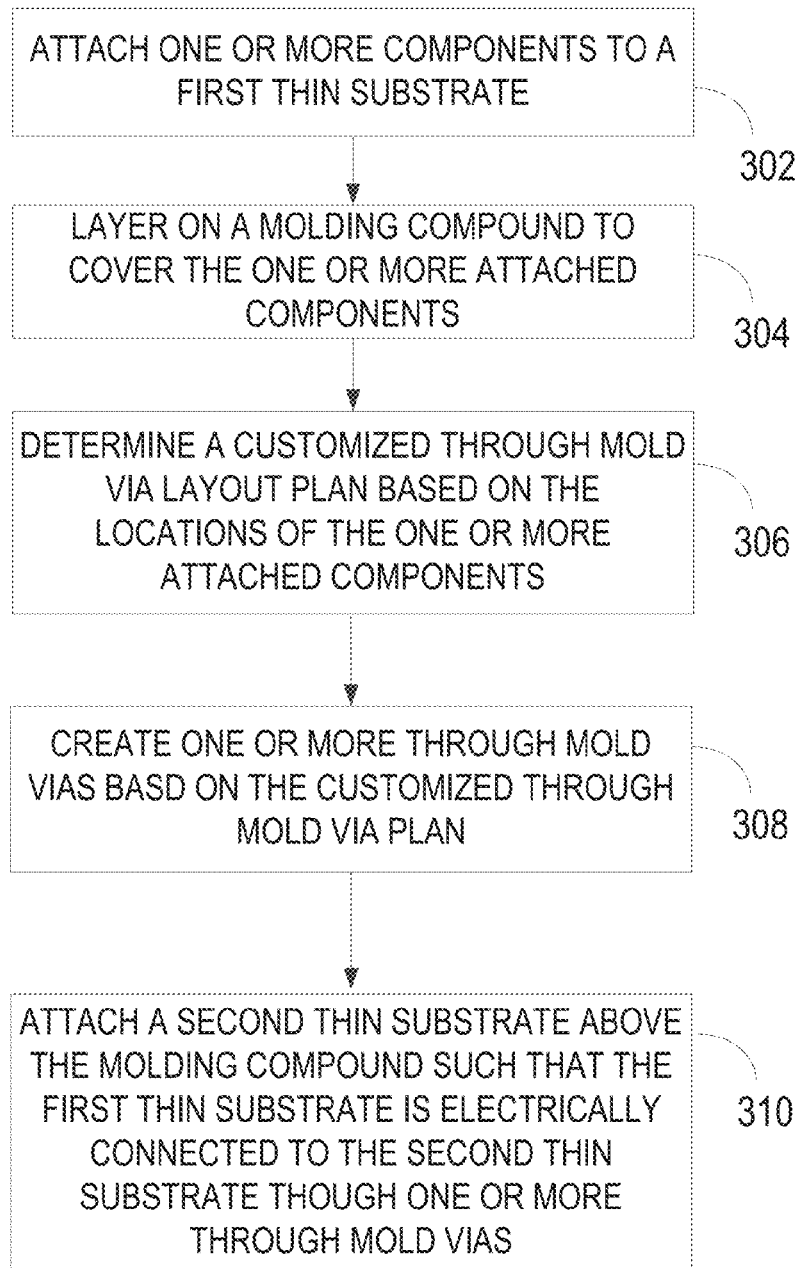


FIG. 3

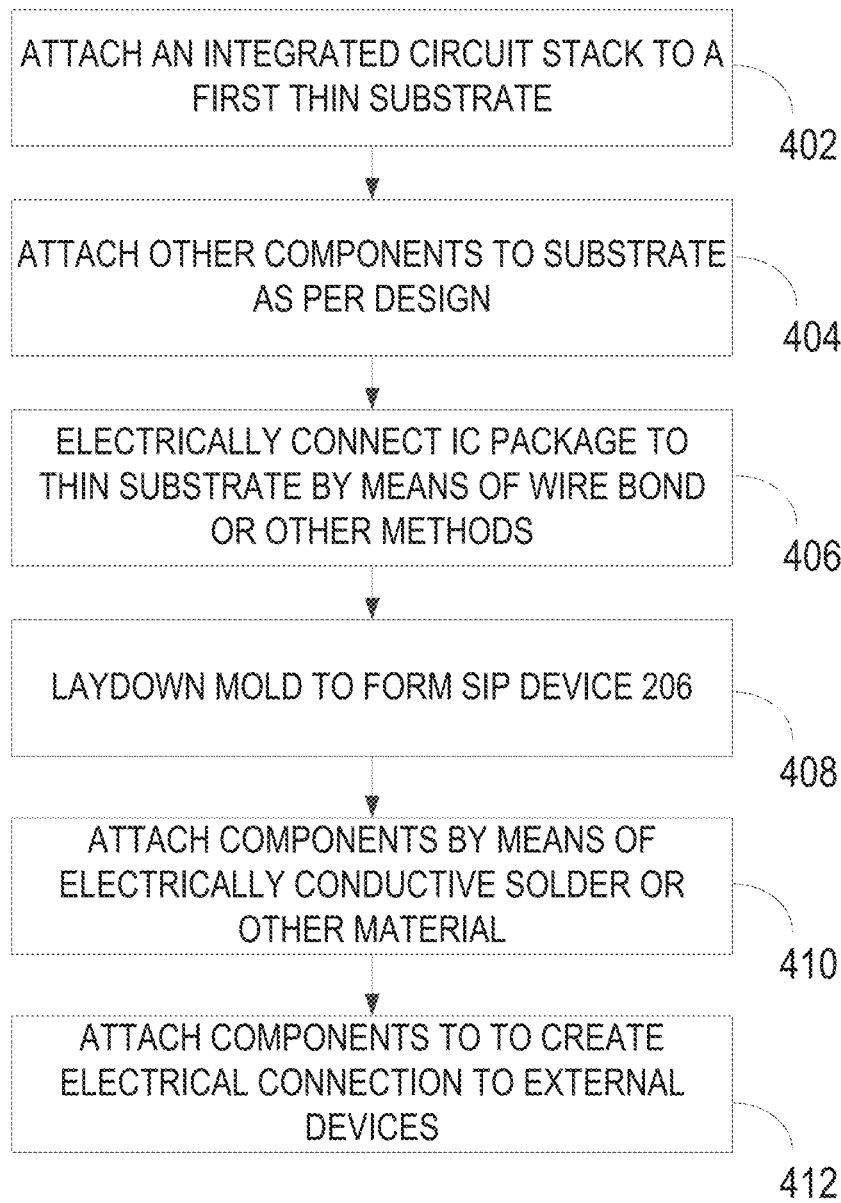


FIG. 4

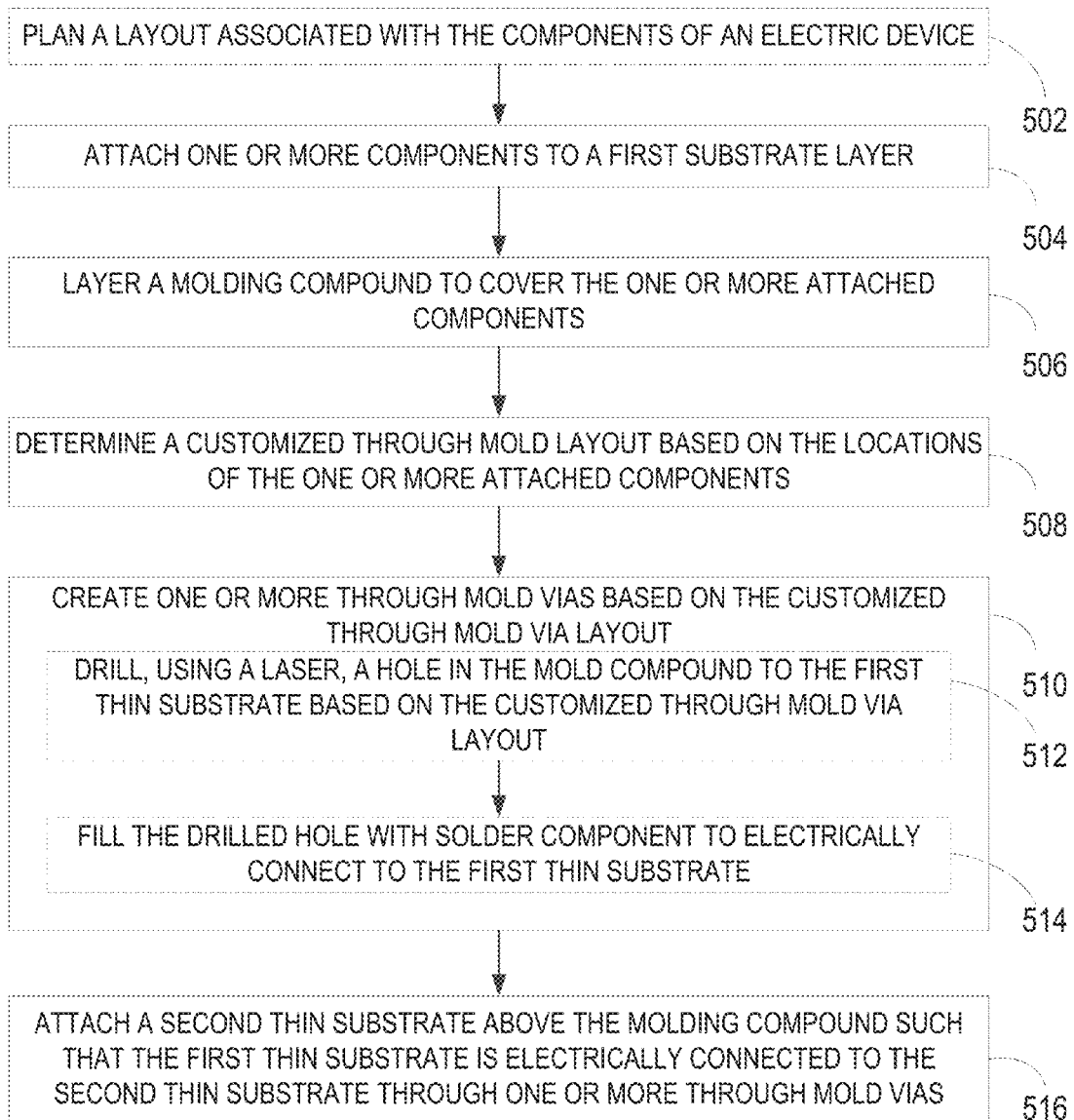


FIG. 5

500

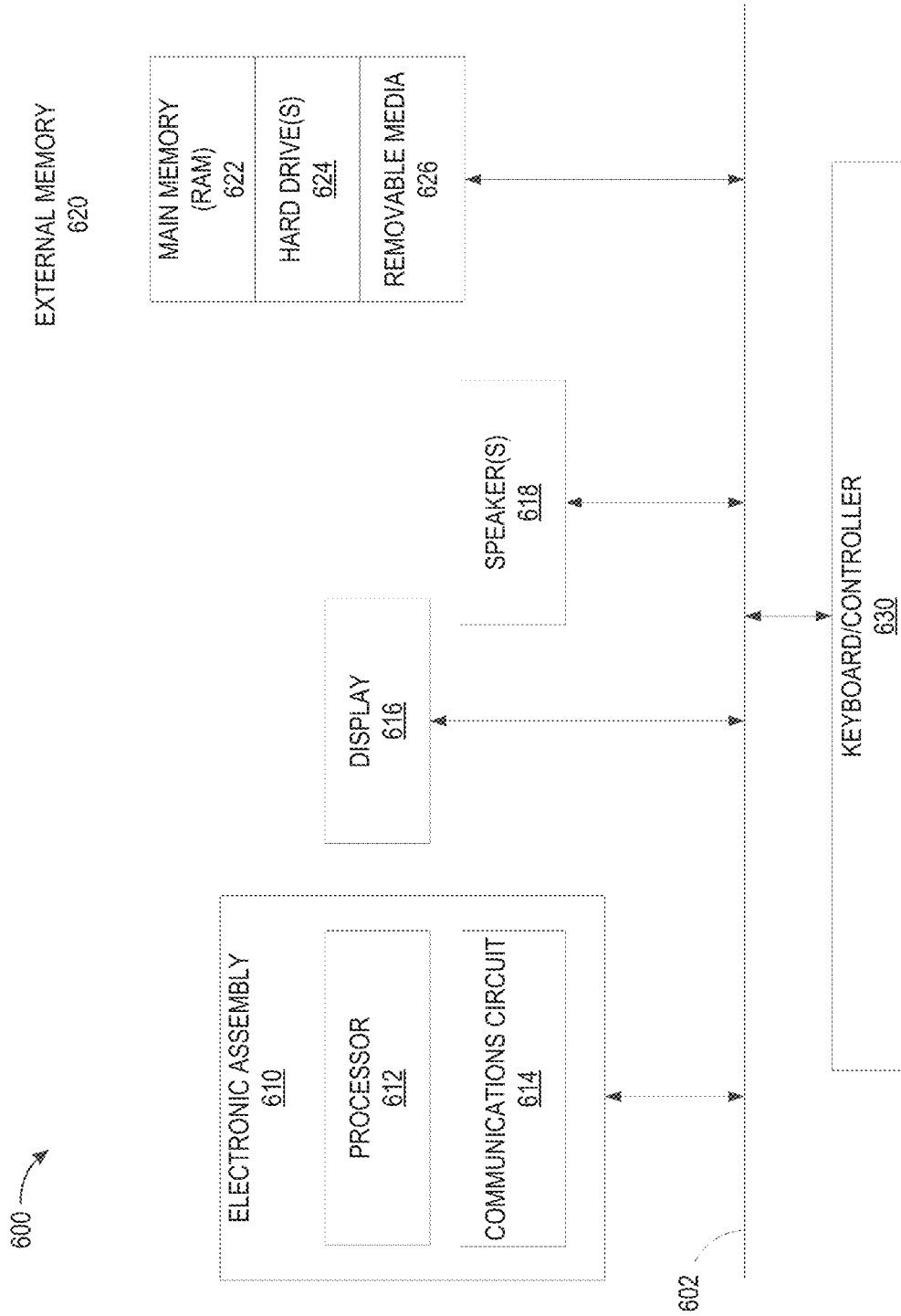


FIG. 6

SOLID STATE DEVICE MINIATURIZATION

PRIORITY

[0001] This Application claims the benefit of priority to U.S. patent application Ser. No. 14/978,315, filed Dec. 22, 2015, which is incorporated by reference herein in its entirety.

TECHNICAL FIELD

[0002] Embodiments described herein generally relate to electrical interconnections in micro electrical devices.

BACKGROUND

[0003] Electronic devices have grown increasingly small and power efficient. As such, each component within an electronic device (e.g., a smart phone, laptop, tablet, or other size dependent device) needs to be developed in smaller sizes. In an effort to decrease the size of various electric components a variety of strategies have been used. Thus, any strategy that enables further reduction in size is important.

[0004] For example, solid state drives (SSDs) have been developed in smaller form factors for use in ultrabooks, tablets, 2 in 1s, and so on. The standard 1.8 inch and 2.5 inch form factors were developed to meet the need for smaller form factors. More recently, caseless form factors have been developed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0005] FIGS. 1A-1B shows a cross-sectional representation of an electric device.

[0006] FIG. 2 shows a cross-sectional representation of an electric device 200.

[0007] FIG. 3 is a flow diagram illustrating a method, in accordance with some example embodiments, for creating a miniature solid state device.

[0008] FIG. 4 is a flow diagram illustrating a method, in accordance with some example embodiments, for creating a system in a package with a decreased z-height.

[0009] FIG. 5 is a flow diagram illustrating a method, in accordance with some example embodiments, for creating a miniature solid state device.

[0010] FIG. 6 is block diagram of an electronic system in accordance with some example embodiments.

DESCRIPTION OF EMBODIMENTS

[0011] The following description and the drawings sufficiently illustrate specific embodiments to enable those skilled in the art to practice them. Other embodiments may incorporate structural, logical, electrical, process, and other changes. Portions and features of some embodiments may be included in, or substituted for, those of other embodiments. Embodiments set forth in the claims encompass all available equivalents of those claims.

[0012] There is significant incentive to make electric devices in small form factors to enable more convenient consumer devices. Solid state drive devices are a type of electric devices for which size is an increasingly important factor. These devices are used in a variety of electronic devices including personal computers, smart phones, tablets, laptops, personal music players, and so on.

[0013] In this example, the solid state drive has been moved into a caseless form factor so that the overall profile

size (z-height) can be reduced. This electric device includes two thin substrates. The thin substrates are designed to be thinner than typical substrates and as thin as 0.3 millimeters in thickness or even thinner depending on design requirements. The first thin substrate is positioned at the bottom of the device. The second thin substrate is positioned at the top of the device. In some example embodiments, the thin substrates are printed circuit boards (PCBs).

[0014] One or more components are physically, electrically, and communicatively coupled to the first thin substrate. In some example embodiments, the components include one or more active components such as transistors, diodes, field-effect transistors (FETs), other discrete semiconductors, integrated circuits, and so on. In some example embodiments, the components include one or more passive components such as resistors.

[0015] The space between the first thin substrate (to which one or more components are attached) and the second thin substrate (which is positioned above the first thin substrate) is filled with mold compound. Thus, this mold compound fills the empty space between the lower (first) thin substrate and upper (second) thin substrate.

[0016] In some example embodiments, through mold vias (TMVs) are drilled through the mold. In some example embodiments, the drilled TMVs are then filled with a conductive material to electronically and communicatively connect the second thin substrate and the first thin substrate (e.g., connecting the top substrate to the bottom substrate for communication).

[0017] The through mold vias can be placed anywhere in the electric device. With the freedom to customize the location of TMVs within the electric device, there is an increased amount of space available for components in between the first thin substrate and the second thin substrate. With the increased amount of available space in between the two substrates, the electric device can be configured to smaller and more efficient form factors.

[0018] Thus, the total size of the electric piece is shrunk by including one or more components between the upper and lower substrates. Indeed, in some cases, all components can be fit between the two substrates such that the total profile (or z-height) of the electric device is similar to the thickness of the substrate alone in previous technologies. This drastic decrease in size allows these electric devices to be used in smaller devices and in more creative ways.

[0019] In some example embodiments, an entire system is put into a single package to create a system-in-package (SiP). SiPs are then connected to a substrate that allows them to be used in larger devices. Thus, SiPs can be fit into different form factors. Being able to adopt one SiP device to multiple form factors and thus multiple market segments increases the usefulness of the SiP.

[0020] In some example embodiments, the height (z-height) can be reduced by using two thin substrates. The first thin substrate is placed on the bottom and is connected through solder connections to the second thin substrate which is placed above the first thin substrate. The second thin substrate includes at least one gap or hole such that it does not cover the first thin substrate (the lower substrate) completely. Instead, at least one section of the first thin substrate is visible through the second thin substrate when viewed from above.

[0021] The SiP is then connected to the first thin substrate (e.g., physically and communicatively) at a position match-

ing that of the gap in the second thin substrate, such that the SiP protrudes through the gap in the second thin substrate. In this way, the total height of the SiP package is reduced to the height of the first thin substrate plus the height of the SiP. Thus, if the first thin substrate is 0.3 mm thick and the SiP is 0.6 mm high, the total height is 0.9 mm. Previously SiP components could be much thicker with, for example, a 0.8 mm substrate and a 1.2 mm SiP.

[0022] FIG. 1A shows a cross-sectional representation of an electric device **100**. In some example embodiments, the electric device **100** is a solid state drive that provides memory services. The electric device **100** includes two thin substrates. The first thin substrate **102** is positioned at the bottom of the electric device **100**. The second thin substrate **104** is positioned above the first thin substrate **102**. Each substrate is composed of a thin slice of an electrical insulator or semiconductor such as silicon, silicon dioxide, aluminum oxide, sapphire, germanium, gallium arsenide, an alloy of silicon and germanium, indium phosphide, or other appropriate substrate material.

[0023] In some example embodiments, the thin substrates (both the first **102** and the second **104**) are thinner than typical substrates in electrical devices **100**. For example, a typical substrate may be 0.8 millimeters in thickness. The first thin substrate **102** and the second thin substrate **104** are as thin as 0.3 mm.

[0024] One or more components (**106-1** to **106-3**) are then attached to the first thin substrate **102**. In some example embodiments, the components **106-1** to **106-3** are connected to the first thin substrate **102** electrically, physically, and communicatively, such that each component **106-1** to **106-3** is able to communicate with other components **106-1** to **106-3** of the electrical device **100**. In some example embodiments, the components **106-1** to **106-3** are electrically connected to the first thin substrate **102** via one or more wire bonds **108-1** to **108-2**. In some example embodiments, the components **106-1** to **106-3** can be connected to the first thin substrate by other methods, such as a flip chip interconnect.

[0025] In some example embodiments, the second thin substrate **104** includes a gap or hole, where it does not overlap vertically with the first thin substrate **102**. For example, when viewed from above, the second thin substrate may include a gap or hole that allows the first thin substrate to be visible.

[0026] In other example embodiments, the second thin substrate **104** includes two separate thin substrate **104** and **105** that each cover a portion of the first thin substrate **102** but are not connected. In yet other examples, it is possible to have a gap or hole in the middle of the second thin substrate but still have both ends of the substrate (**104** and **105** in this case) connected around the hole.

[0027] In some example embodiments, a molding compound **120** is used to fill in space between the first thin substrate **102** and the second thin substrate **104**.

[0028] In some example embodiments, one or more through mold vias (TMVs) are drilled into through the molding compound **120**. The TMVs can be filled with an electrically conductive material (e.g., solder) such that the first thin substrate **102** is communicatively coupled to the second thin substrate **104**.

[0029] Each TMV can be placed in a customized position within the molding compound **120**. In this way, the components **106-1** to **106-3** on the first thin substrate **102** (e.g., **106-1** to **106-3**, **116**, and so on) can be placed as needed and

the through mold vias can be placed through the mold **120** wherever needed. In some example embodiments, the through mold vias are made based on the layout of the components **106-1** to **106-3** and the level of communication needed.

[0030] In some example embodiments, the electric device **100** includes one or more edge connectors (**114-1** to **114-2**) that connect the electric device **100** to an outside device. For example, the electric device **100** uses the edge connector **114-1**, **114-2** (e.g., made of a conductive material such as copper) to communicate to a smart phone in which it is inserted as a memory storage device.

[0031] In some example embodiments, the electric device **100** includes ground connectors that connect **122-1** and **122-2** the electric components **106-1** to **106-3** of the electric device **100** to the ground.

[0032] In some example embodiments, the electric device **100** also includes passive devices **116** (e.g., such as a resistor) attached to the first thin substrate **102**.

[0033] FIG. 1B shows a cross-sectional representation of an electric device **100**, that is a variation of the electric device **100** shown in FIG. 1A. In some example embodiments, the electric device **100** is a solid state drive that provides memory services.

[0034] The electric device **100** includes two thin substrates. The first thin substrate **102** is positioned at the bottom of the electric device **100**. The second thin substrate **104** is positioned above the first thin substrate **102**. As discussed above in reference to FIG. 1A, the thin substrates (both the first **102** and the second **104**) are thinner than typical substrates in electrical devices **100**. For example, a typical substrate may be 0.8 millimeters in thickness. The first thin substrate **102** and the second thin substrate **104** are as thin as 0.3 mm.

[0035] As above, one or more components (**106-1** to **106-3**) are then attached to the first thin substrate **102** and the components **106-1** to **106-3** are electrically connected to the first thin substrate **102** via one or more wire bonds **108-1** to **108-2**. In some example embodiments, a molding compound **120** is used to fill in space between the first thin substrate **102** and the second thin substrate **104**.

[0036] In some example embodiments, one or more through mold vias (TMVs) are drilled into through the molding compound **120**. The electric device **100** includes one or more edge connectors (**114-1** to **114-2**) that connect the electric device **100** to an outside device. For example, the electric device **100** uses the edge connectors **114-1**, **114-2** (e.g., made of a conductive material such as copper) to communicate to a smart phone in which it is inserted as a memory storage device. In some example embodiments, the electric device **100** also includes passive devices **116** (e.g., such as a resistor) attached to the first thin substrate **102**.

[0037] In this example embodiment, one or more components **112-1** to **112-3** are connected to the second thin substrate **104**. These components **112-1** to **112-3** include one or more surface mounted devices (SMD) including transistors, diodes, field-effect transistors (FETs), other discrete semiconductors, integrated circuits and so on.

[0038] In some example embodiments, one or more passive components **118** are also connected to the second thin substrate **104**. In some example embodiments, the passive components **118** include resistors, capacitors, and inductors.

[0039] In some example embodiments, the active components (**112-1** to **112-3**) are mechanically fixed and electrically

cally connected to the second thin substrate **104** using soldering. In some example embodiments, a variety of soldering techniques can be used to attach the components **112-1** to **112-3** to the second thin substrate **104**. For example, through-hole technology is used to insert component leads in holes or gaps in the PCB which are then filled with solder.

[0040] In other example embodiments, surface-mount technology (SMT) is used and the components **112-1** to **112-3** are glued on pads or leads on the surface of the PCB.

[0041] In the current example, the active components (**112-1** to **112-3**) have been attached to the second thin substrate **104** with a ball grid array. A ball grid array is a series of regularly spaced solder points that connect a component (e.g., memory, ASIC) to the PCB. This allows the active components **112-1** to **112-3** to communicate with both the first thin substrate **102** and with outside electrical devices via the edge connectors **114-1** and **114-2**.

[0042] FIG. 2 shows a cross-sectional representation of an electric device **200**. In this example, the depicted electric device **200** is a system in a package (SIP). A SIP performs all or most of the functions of an electric system **200**. In a SIP the integrated circuit dies can be stacked vertically (as opposed to horizontally spaced along a substrate) to conserve space and improve communication efficiency.

[0043] The SIP includes a die stack **208**. The die stack **208** includes an application-specific integrated circuit **210**, one or more components **212-1** to **212-3** including one or more passive components **118** (e.g., resistors, capacitors, inductors, and so on) or active components **112-1** to **112-3** (e.g., diodes and so on).

[0044] In some example embodiments, the die stack **208** includes one or more different dies including NAND memory, DRAM, or other integrated circuits.

[0045] In some example embodiments, the SIP **206** also includes a variety of miscellaneous components (**216-1** and **216-2**) that serve the various purposes of the SIP **206** such as resistors, inductors, capacitors, voltage regulators, thermal sensors, interposers (another PCB or substrate with active/passive components), and so on

[0046] In some example embodiments, the SIP **206** is connected to a first thin substrate **202**. Each substrate is composed of a thin slice of an electrical insulator or semiconductor such as silicon, silicon dioxide, aluminum oxide, sapphire, germanium, gallium arsenide, an alloy of silicon and germanium, indium phosphide, or other appropriate substrate material. In some example embodiments, the die stack **208** is connected to the first thin substrate **202** by a wire bond **218** that connects the die stack **208** to the first thin substrate **202** electrically and communicatively.

[0047] In some example embodiments, the first thin substrate **202** is connected to a second thin substrate (**204-1** and **204-2**) positioned above it. The two substrates are connected with a series of solder joints **220** that connect the first thin substrate **202** and the second substrate **204** together physically, electrically, and communicatively. In this way, the components **212-1** to **212-3** connected to the first thin substrate **202** can communicate to components attached to the second thin substrate (**204-1** to **204-2**).

[0048] In some example embodiments, the first thin substrate **202** and the second thin substrate **204** are both connected to an edge connector **222-1** and **222-2**. The edge connectors **222-1** and **222-2** allows the electric device **200** to outside electric devices and components.

[0049] FIG. 3 is a flow diagram illustrating a method, in accordance with some example embodiments, for creating a miniature solid state device. Each of the operations shown in FIG. 3 may correspond to manufacturing steps carried out during the creation of an electric device **100**.

[0050] In some example embodiments, one or more components **106-1** to **106-3** and **116** are attached (**302**) to a first thin substrate **102**. In some example embodiments, components include both active components **106-1** to **106-3** such as diodes, FETs, ICs, and passive components **116** such as resistors, capacitors, and inductors.

[0051] Each component is attached to the thin substrate using through-hole technology, surface mount technology, solder, adhesive attach or a combination of these methods. In some example embodiments, the components **106-1** to **106-3** are electrically connected to the substrate through a wire bond **108-1**.

[0052] Once the components **106-1** to **106-3** are attached to the first thin substrate **102**, a molding compound **120** layered (**304**) on top of the one or more components **106-1** to **106-3**, such that the molding compound **120** covers the one or more components **106-1** to **106-3**. The over molding compound is polymeric compounds.

[0053] Once the over mold component has been layered on, a customized through mold via (TMV) plan is determined (**306**) based on the locations of the one or more attached components **106-1** to **106-3**. In this way, the TMVs can be placed wherever needed, so long as no components **106-1** to **106-3** and **116** are current placed in that location. In some example embodiments, the position of the components **106-1** to **106-3** and the position of the TMVs are planned simultaneously to maximize efficiency.

[0054] Using customized TMV placement allows components **106-1** to **106-3** to be placed within a larger total space than otherwise would normally be available. In this way, the components **106-1** to **106-3** can be placed as needed and the TMVs can be placed in the portions not occupied by components **106-1** to **106-3**, wherever they are.

[0055] One or more through mold vias (**110-1** to **110-5**) are created based on the customized through mold via plan (**308**). In some example embodiments, the TMVs are created by using a laser to drill through the molding to the thin substrate below. The thin substrate is designed to have contacts on the substrate where the holes are going to be drilled by the laser.

[0056] In some example embodiments, the holes created by the laser drilling are filled with solder compound (or any electrically conductive material). The entire electric device **100** can then be heated to reflow the solder compound.

[0057] A second thin substrate **104** is then attached (**310**) over the molding compound **120** such that the second thin substrate **104** is electrically connected to the first thin substrate **102** through the one or more through mold vias (**110-1** to **110-5**).

[0058] FIG. 4 is a flow diagram illustrating a method, in accordance with some example embodiments, for creating a system in a package with a decreased z-height. Each of the operations shown in FIG. 4 may correspond to manufacturing steps carried out during the creation of an electric device **200**.

[0059] In some example embodiments, an integrated circuit stack (e.g., stack **214** in FIG. 2) is attached (**402**) to a first thin substrate (e.g., substrate **202** in FIG. 2). In some example embodiments, the IC stack is mechanically fixed

and electrically connected to the thin substrate **204** using one of a variety of soldering techniques. In other example embodiments, another connection method such as through-hole technology or surface mount technology is used to fix the IC stack **214** to the first thin substrate.

[0060] Once the IC stack has been attached to the substrate, one or more other components (such as **216-1**, **216-2**, **212-1**, **212-3**, **210**, and son on as seen in FIG. 2) are connected (**404**) to either the first thin substrate **202** or substrate **208** as needed.

[0061] In some example embodiments, the IC package (e.g., package **214** as seen in FIG. 2) is electrically connected (**406**) to the first thin substrate (e.g., substrate **202** in FIG. 2) via a wire bond (e.g., the wire bond **218** in FIG. 2) or the electrical connection methods.

[0062] In some example embodiments, a layer of mold is laid down (**408**) to form the SiP device **206**. Once the SiP has been fully formed, a second thin substrate (e.g., the thin substrate **204-1** in FIG. 2) is attached to the first thin substrate (e.g., the thin substrate **202** in FIG. 2) by electrically conductive solder or other connection materials or techniques.

[0063] In some example embodiments, a third thin substrate (e.g., the thin substrate **204-2** in FIG. 2) is connected to the first thin substrate (e.g., the thin substrate **202** in FIG. 2) so as to leave a gap or hole in the upper thin substrate layer.

[0064] One or more components (e.g., components **222-1** and **222-2** in FIG. 2) are attached to the second thin substrate (e.g., the thin substrate **204-1** in FIG. 2). The one or more components (e.g., components **222-1** and **222-2** in FIG. 2) are edge connectors that connect the SiP **206** to one or more external devices.

[0065] FIG. 5 is a flow diagram **500** illustrating a method, in accordance with some example embodiments, for creating a miniature solid state device. Optional operations are indicated by dashed lines (e.g., boxes with dashed-line borders). In some embodiments, the method described in FIG. 5 is performed during the manufacturing of an electrical device **100**. The method described can also be performed by any other suitable configuration of hardware.

[0066] In some example embodiments, a layout associated with the components **106-1** to **106-3** of an electric device (e.g., device **100** of FIG. 1B) is planned (**502**). Thus, the particular components **106-1** to **106-3** to be added to the electric device (e.g., the device **100** in FIG. 1B) as well as their respective layouts are determined based on the intended use and needs of the electric device (e.g., the device **100** in FIG. 1B). In some example embodiments, the layout is determined automatically based on one or more component layout algorithms.

[0067] In some example embodiments, a manufacturing device or system associated with manufacturing the electric device (e.g., the device **100** in FIG. 1B) attaches (**504**) one or more components **106-1** to **106-3** to a first substrate layer **102**.

[0068] Each component is attached to the thin substrate using through-hole technology, surface mount technology, solder, adhesive attach or a combination of these methods. In some example embodiments, the components **106-1** to **106-3** are electrically connected to the substrate through a wire bond **108-1** to **108-2**.

[0069] In some example embodiments, components **106-1** to **106-3** are mechanically fixed and electrically connected to

the second thin substrate **104** using soldering. In some example embodiments, a variety of soldering techniques can be used to attach the components **106-1** to **106-3** to the second thin substrate **104**. For example, through-hole technology is used to insert component leads in holes or gaps in the PCB and are then filled with solder.

[0070] In other example embodiments, surface-mount technology (SMT) are used and the components **106-1** to **106-3** are glued on pads or leads on the surface of the PCB. In the yet other examples, the components **106-1** to **106-3** can be attached to the second thin substrate **104** with a ball grid array. A ball grid array is a series of regularly spaced solder points that connect a component (e.g., solid state memory) to the PCB.

[0071] In some example embodiments, the first thin substrate layers and the second thin substrate layers are thin printed circuit boards. In some example embodiments, the first thin substrate layer and the second thin substrate layer are less than 0.5 millimeters thick.

[0072] In some example embodiments, a manufacturing device or system associated with manufacturing the electric device (e.g., the device **100** in FIG. 1B) layers (**506**) a molding compound **120** to cover the one or more attached components **106-1** to **106-3**. In some example embodiments, the molding component is a polymeric compound and is non-conductive.

[0073] In some example embodiments, the manufacturing device or system determines (**508**) a customized through mold layout based on the locations of the one or more attached components **106-1** to **106-3**. In some example embodiments, the customized through mold via layout is created simultaneously with planning the layout of the one or more components **106-1** to **106-3**. Thus, when the electric device (e.g., the device **100** in FIG. 1B) is being laid out (e.g., the placement of the components **106-1** to **106-3** is determined) the placement of the TMVs is simultaneously determined to ensure that the TMVs are place appropriately.

[0074] In some example embodiments, one or more TMVs are created based on the customized through mold via layout (**510**). In some example embodiments, creating one or more TMVs includes drilling, using a laser, a hole in the mold compound to the first thin substrate **102** based on the customized through mold via layout (**512**). In some example embodiments, the hole for the TMV can be drilled by a mechanical drill or other methods.

[0075] Once the through mold vias have been drilled by a laser, the drilled holes are filled with solder compound to electrically connect to the first thin substrate **102** (**514**). Thus, the solder material is in direct contact, both physically and electrically with the first thin substrate **102**. In some example embodiments, the solder compound is reflowed (by heating) to ensure a good fill.

[0076] A second thin substrate **104** is attached (**516**) above the molding compound **120** such that the first thin substrate **102** is electrically connected to the second thin substrate **104** through one or more through mold vias. In some example embodiments, the second thin substrate **104** only partially covers the first thin substrate **102**. In yet other example embodiments, the second thin substrate **104** is actually two separate substrates that have a gap between them.

[0077] An example of an electronic device using semiconductor chip assemblies and solders as described in the present disclosure is included to show an example of a higher level device application for the described embodi-

ments. FIG. 6 is a block diagram of an electronic device 600 incorporating at least one device and/or method in accordance with at least one disclosed example embodiment. Electronic device 600 is merely one example of an electronic system in which example embodiments can be used. Examples of electronic devices 600 include, but are not limited to personal computers, tablet computers, mobile telephones, game devices, MP3 or other digital music players, etc. In this example, electronic device 600 comprises a data processing system that includes a system bus 602 to couple the various components of the system. System bus 602 provides communications links among the various components of the electronic device 600 and can be implemented as a single bus, as a combination of busses, or in any other suitable manner.

[0078] An electronic assembly 610 is coupled to system bus 602. The electronic assembly 610 can include any circuit or combination of circuits. In one embodiment, the electronic assembly 610 includes a processor 612 which can be of any type. As used herein, “processor” means any type of computational circuit, such as but not limited to a microprocessor, a microcontroller, a complex instruction set computing (CISC) microprocessor, a reduced instruction set computing (RISC) microprocessor, a very long instruction word (VLIW) microprocessor, a graphics processor, a digital signal processor (DSP), multiple core processor, or any other type of processor or processing circuit.

[0079] Other types of circuits that can be included in electronic assembly 610 are a custom circuit, an application-specific integrated circuit (ASIC), or the like, such as, for example, one or more circuits (such as a communications circuit 614) for use in wireless devices like mobile telephones, personal data assistants, portable computers, two-way radios, and similar electronic systems. The IC can perform any other type of function.

[0080] The electronic device 600 can also include an external memory 620, which in turn can include one or more memory elements suitable to the particular application, such as a main memory 622 in the form of random access memory (RAM), one or more hard drives 624, and/or one or more drives that handle removable media 626 such as compact disks (CD), flash memory cards, digital video disk (DVD), and the like.

[0081] In some example embodiments, the hard drive 624 and/or the removable media 626 include solid state memory devices similar to device 100 discussed in FIGS. 1A and 1B.

[0082] In addition, the electronic assembly 610 can include a system in a package (SiP) similar to the one described as SiP 200 in FIG. 2.

[0083] The electronic device 600 can also include a display device 616, one or more speakers 618, and a keyboard and/or controller 630, which can include a mouse, trackball, touch screen, voice-recognition device, or any other device that permits a system user to input information into and receive information from the electronic device 600.

Term Usage

[0084] Throughout this specification, plural instances may implement components, operations, or structures described as a single instance. Although individual operations of one or more methods are illustrated and described as separate operations, one or more of the individual operations may be performed concurrently, and nothing requires that the operations be performed in the order illustrated. Structures and

functionality presented as separate components in example configurations may be implemented as a combined structure or component. Similarly, structures and functionality presented as a single component may be implemented as separate components. These and other variations, modifications, additions, and improvements fall within the scope of the subject matter herein.

[0085] Although an overview of the inventive subject matter has been described with reference to specific example embodiments, various modifications and changes may be made to these embodiments without departing from the broader scope of embodiments of the present disclosure. Such embodiments of the inventive subject matter may be referred to herein, individually or collectively, by the term “invention” merely for convenience and without intending to voluntarily limit the scope of this application to any single disclosure or inventive concept if more than one is, in fact, disclosed.

[0086] The embodiments illustrated herein are described in sufficient detail to enable those skilled in the art to practice the teachings disclosed. Other embodiments may be used and derived therefrom, such that structural and logical substitutions and changes may be made without departing from the scope of this disclosure. The Detailed Description, therefore, is not to be taken in a limiting sense, and the scope of various embodiments is defined only by the appended claims, along with the full range of equivalents to which such claims are entitled.

[0087] As used herein, the term “or” may be construed in either an inclusive or exclusive sense. Moreover, plural instances may be provided for resources, operations, or structures described herein as a single instance. Additionally, boundaries between various resources, operations, modules, engines, and data stores are somewhat arbitrary, and particular operations are illustrated in a context of specific illustrative configurations. Other allocations of functionality are envisioned and may fall within a scope of various embodiments of the present disclosure. In general, structures and functionality presented as separate resources in the example configurations may be implemented as a combined structure or resource. Similarly, structures and functionality presented as a single resource may be implemented as separate resources. These and other variations, modifications, additions, and improvements fall within a scope of embodiments of the present disclosure as represented by the appended claims. The specification and drawings are, accordingly, to be regarded in an illustrative rather than a restrictive sense.

[0088] The foregoing description, for the purpose of explanation, has been described with reference to specific example embodiments. However, the illustrative discussions above are not intended to be exhaustive or to limit the possible example embodiments to the precise forms disclosed. Many modifications and variations are possible in view of the above teachings. The example embodiments were chosen and described in order to best explain the principles involved and their practical applications, to thereby enable others skilled in the art to best utilize the various example embodiments with various modifications as are suited to the particular use contemplated.

[0089] It will also be understood that, although the terms “first,” “second,” and so forth may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one

element from another. For example, a first contact could be termed a second contact, and, similarly, a second contact could be termed a first contact, without departing from the scope of the present example embodiments. The first contact and the second contact are both contacts, but they are not the same contact.

[0090] The terminology used in the description of the example embodiments herein is for the purpose of describing particular example embodiments only and is not intended to be limiting. As used in the description of the example embodiments and the appended claims, the singular forms “a,” “an,” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will also be understood that the term “and/or” as used herein refers to and encompasses any and all possible combinations of one or more of the associated listed items. It will be further understood that the terms “comprises” and/or “comprising,” when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

[0091] As used herein, the term “if” may be construed to mean “when” or “upon” or “in response to determining” or “in response to detecting,” depending on the context. Similarly, the phrase “if it is determined” or “if [a stated condition or event] is detected” may be construed to mean “upon determining” or “in response to determining” or “upon detecting [the stated condition or event]” or “in response to detecting [the stated condition or event],” depending on the context.

1. (canceled)
2. A memory device, comprising:
 - a first substrate layer;
 - a second substrate layer positioned proximate the first substrate layer such that a space is formed between the first substrate layer and the second substrate layer, wherein the second substrate layer is in electrical communication with the first substrate layer;
 - one or more components positioned in the space;
 - an overmold compound forming a direct interface with the one or more components; and
 - one or more edge connectors coupled to an exterior surface of a first end of the memory device and positioned proximate the edge of the first substrate layer, wherein the one or more edge connectors are configured to be in electrical communication with the one or more components.
3. The memory device of claim 2, wherein the one or more components includes a die stack.
4. The memory device of claim 2, wherein a portion of the one or more components extends through a hole in the second substrate.
5. The memory device of claim 2, wherein at least one of the one or more components are positioned within a footprint of a hole in the second substrate.
6. The memory device of claim 2, wherein the one or more components includes NAND memory or DRAM memory.
7. The memory device of claim 2, wherein the one or more components include passive components.

8. The memory device of claim 2, wherein the one or components positioned in the space is a first set of components, and further comprising a second set of components positioned on the second substrate.

9. The memory device of claim 2, wherein the one or more edge connectors are coupled to the first substrate layer and the second substrate layer.

10. The memory device of claim 2, wherein the one or more edge connectors are coplanar with an edge of the first substrate.

11. The memory device of claim 2, further comprising one or more ground connectors.

12. The memory device of claim 11, wherein the one or more ground connectors are coupled to an exterior surface of a second end of the memory device and positioned proximate the edge of the first substrate layer.

13. The memory device of claim 2, wherein the one or more ground connectors are coplanar with an edge of the first substrate.

14. The memory device of claim 2, wherein the first substrate layer or the second substrate layer has a thickness of approximately 0.3 millimeters to 0.8 millimeters.

15. The memory device of claim 2, further comprising a first via, wherein the first via is configured to allow the electrical communication between the first substrate layer and the second substrate layer.

16. The memory device of claim 15, wherein the first via is a through mold via, and the through mold via forms a direct interface with the overmold compound.

17. The memory device of claim 15, further comprising a second via, wherein the second via is configured to allow the electrical communication between the first substrate layer and a third substrate layer, wherein the third substrate layer is coplanar with the second substrate layer.

18. An electronic system, comprising:

a memory device, including:

- a first substrate layer;
- a second substrate layer positioned proximate the first substrate layer such that a space is formed between the first substrate layer and the second substrate layer, wherein the second substrate layer is in electrical communication with the first substrate layer;
- one or more components positioned in the space;
- an overmold compound forming a direct interface with the one or more components;
- one or more edge connectors coupled to an exterior surface of a first end of the memory device and positioned proximate the edge of the first substrate layer, wherein the one or more edge connectors are configured to be in electrical communication with the one or more components;
- a processor in electrical communication with the memory device.

19. The memory device of claim 18, wherein the one or more components includes a die stack.

20. The memory device of claim 18, wherein the one or more edge connectors are coplanar with an edge of the first substrate.

21. The memory device of claim 18, wherein the first substrate layer or the second substrate layer has a thickness of approximately 0.3 millimeters to 0.8 millimeters.